

N0032H Process Geometry

Features

- Low Input Capacitance: 6.0pF Typical
- Low Gate Leakage: 10pA Typical
- High Breakdown Voltage: -60V Typical
- Small Die: 416um X 416um X 203um
- Bond Pads: 90um X 90um
- Substrate Connected to Gate
- Au Back-Side Finish

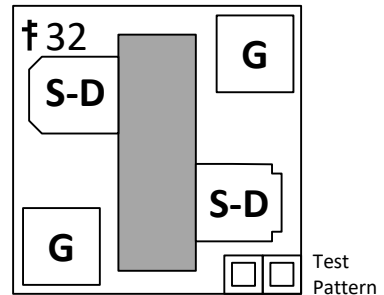
Applications

- General Purpose Amplifier
- Small Signal Amplifier
- Custom Part Options

Description

The InterFET N0032H Geometry is targeted low leakage general purpose amplifiers. The low input capacitance makes it ideal for higher frequency applications.

Geometry Top View



Standard Parts

- 2N3821, 2N3822
- 2N3823, 2N3824
- 2N4222, 2N4222A

Product Summary

| Parameters | Min | Typ | Max | Unit |
|---|------|-----|-----|------|
| BV _{GSS} Gate to Source Breakdown Voltage | -50 | -60 | | V |
| I _{DSS} Drain to Source Saturation Current | 1 | | 22 | mA |
| V _{GS(off)} Gate to Source Cutoff Voltage | -0.5 | | -10 | V |
| G _{FS} Forward Transconductance | | 5 | | mS |

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

| Parameters | Min | Typ | Max | Unit |
|--|-----|-----|-----|------|
| V _{RGS} Reverse Gate to Source or Drain Voltage | -50 | -60 | | V |
| I _{FG} Continuous Forward Gate Current | | | 10 | mA |
| T _J Operating Junction Temperature | -55 | | 150 | °C |
| T _{STG} Storage Temperature | -65 | | 175 | °C |



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

Electrical Characteristics

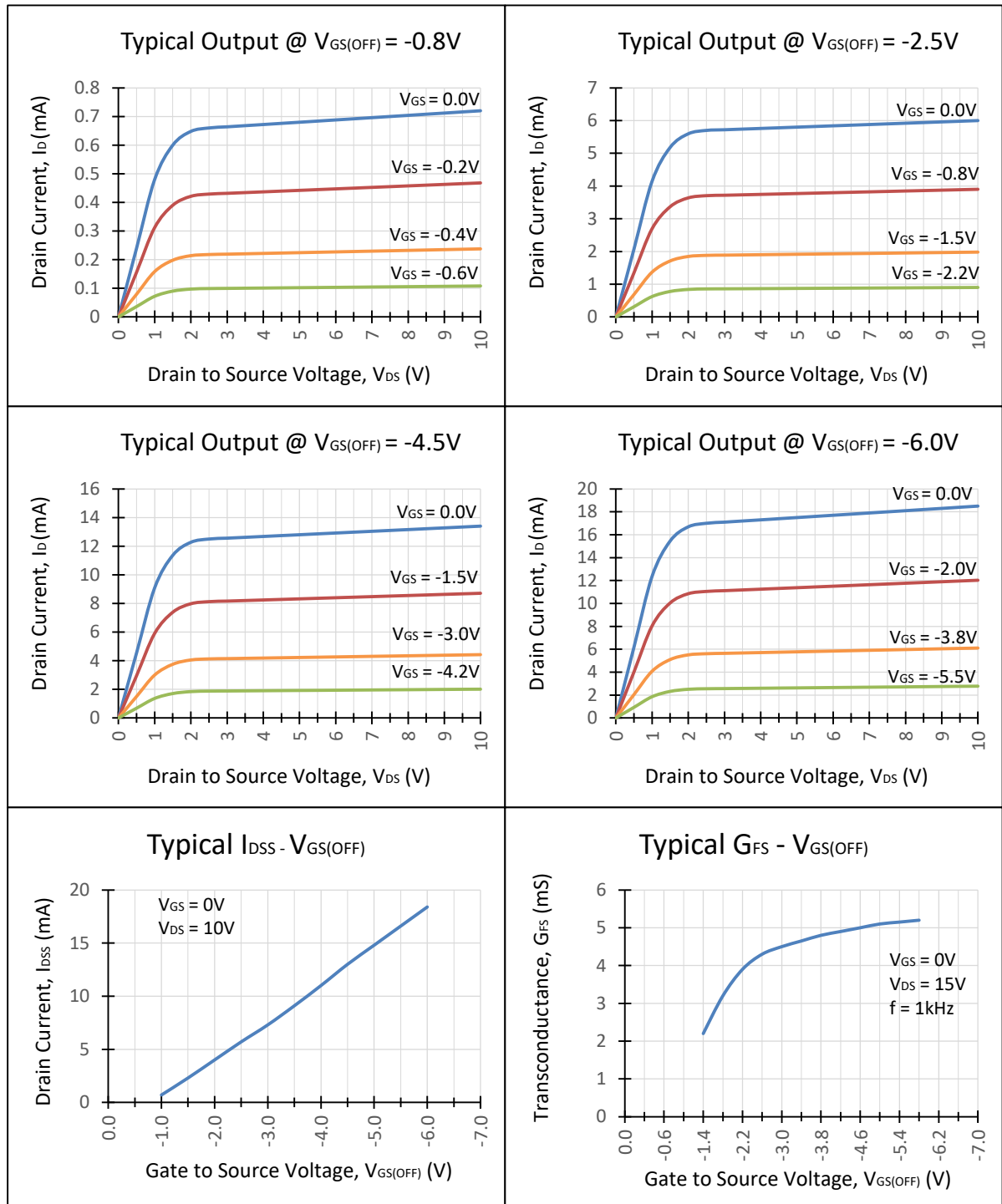
Static Characteristics (@ TA = 25°C, Unless otherwise specified)

| Parameters | Conditions | Min | Typ | Max | Unit |
|--|--|------|-----|------|------|
| BV _{GSS} Gate to Source Breakdown Voltage | I _G = -1μA, V _{DS} = 0V | -50 | -60 | | V |
| I _{GSS} Gate to Source Reverse Current | V _{GS} = -15V, V _{DS} = 0V | | -10 | -100 | pA |
| V _{GS(OFF)} Gate to Source Cutoff Voltage | V _{DS} = 15V, I _D = 1nA | -0.5 | | -10 | V |
| I _{DSS} Drain to Source Saturation Current | V _{DS} = 15V, V _{GS} = 0V | 1 | | 22 | mA |

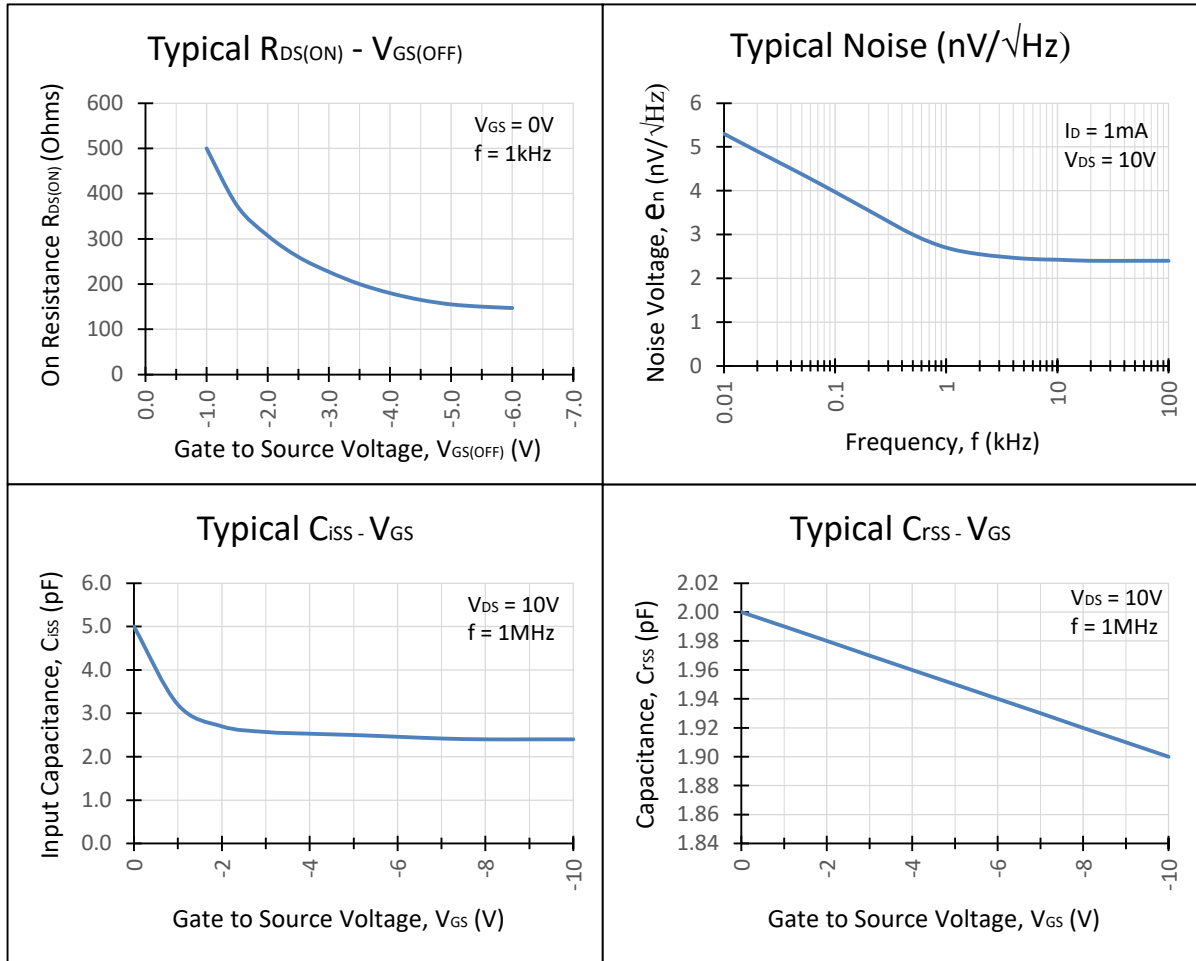
Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

| Parameters | Conditions | Min | Typ | Max | Unit |
|--|--|-----|-----|-----|--------|
| G _{FS} Forward Transconductance | V _{DS} = 15V, V _{GS} = 0V, f = 1kHz | | 5 | | mS |
| C _{iss} Input Capacitance | V _{DS} = 15V, V _{GS} = 0V, f = 1MHz | | 6 | 7 | pF |
| C _{rss} Reverse Transfer Capacitance | V _{DS} = 15V, V _{GS} = 0V, f = 1MHz | | 1.3 | 3 | pF |
| e _n Noise Voltage | V _{DS} = 10V, I _D = 1mA, f = 1kHz | | 2.7 | | nV/√Hz |

Typical N0030H Characteristics

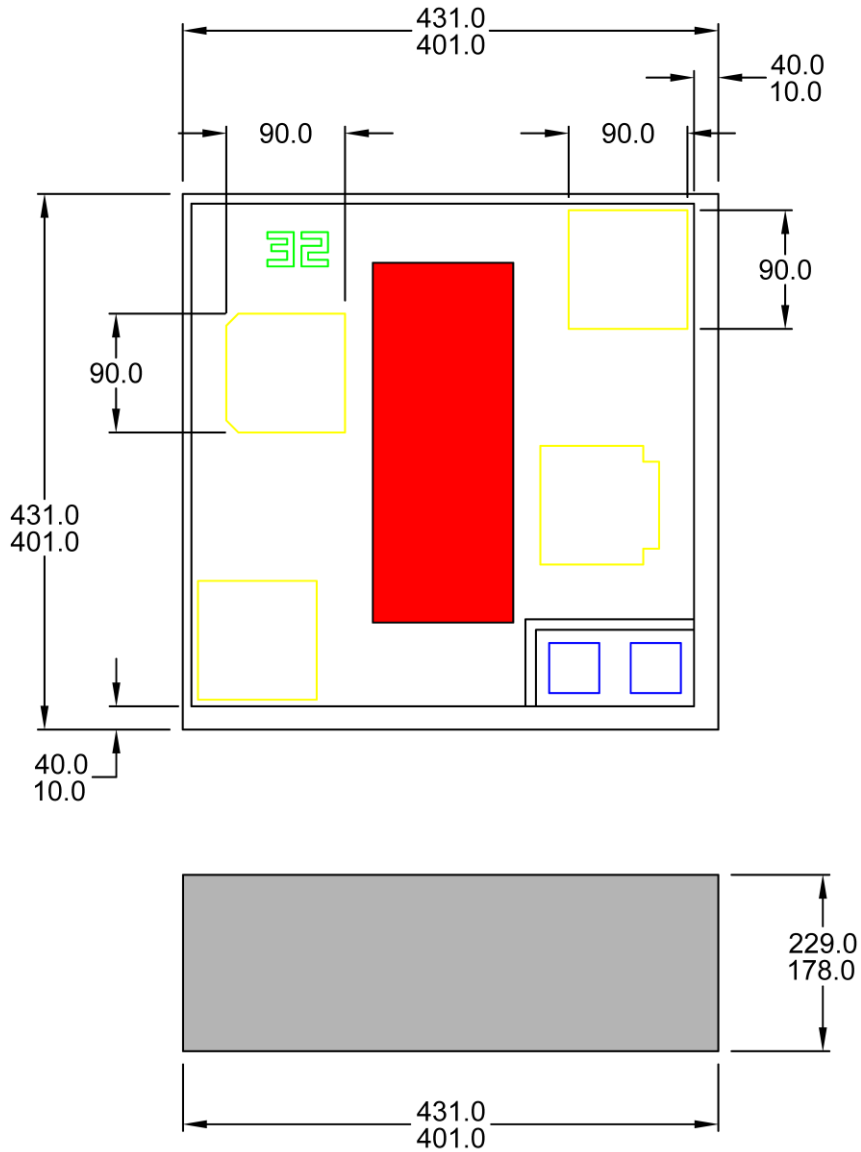


Typical N0030H Characteristics (Continued)



N0032H Die Geometry Mechanical

Raw Die Dimensions



1. All linear dimensions are in micrometers.